Amendments to the Claims:

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-15 (canceled).

Claim 16 (currently amended): A semiconductor device ~~according to claim 15~~, comprising:

an embedded insulation layer formed in a semiconductor substrate;

a plurality of power semiconductor transistors formed on said semiconductor substrate;

a trench isolating between said plurality of power semiconductor transistors formed on said semiconductor substrate on said embedded insulation layer, whereby said plurality of power semiconductor transistors are individually isolated from each other and, isolated from any other semiconductor transistors;

an isolator insulating and driving control electrodes of said power semiconductor transistors and including capacitive coupling provided for transmitting signals between said plurality of power semiconductors transistors;

wherein at least two of said plurality of power semiconductor transistors are each connected to each other in series; and

a drive circuit for driving a control electrode of each of said power semiconductor transistors to suppress driving current supplied to one of said at least two power semiconductor transistors when over current is detected in current flowing in at least another one of said at least two power semiconductor transistors connected in series,

wherein said plurality of power semiconductor transistors drive an ignition coil.

Claim 17 (currently amended): A semiconductor device ~~according to claim 15~~, , comprising:

an embedded insulation layer formed in a semiconductor substrate;

a plurality of power semiconductor transistors formed on said semiconductor substrate;

a trench isolating between said plurality of power semiconductor transistors formed on said semiconductor substrate on said embedded insulation layer, whereby said plurality of power semiconductor transistors are individually isolated from each other and, isolated from any other semiconductor transistors;

an isolator insulating and driving control electrodes of said power semiconductor transistors and including capacitive coupling provided for transmitting signals between said plurality of power semiconductors transistors;

wherein at least two of said plurality of power semiconductor transistors are each connected to each other in series; and

a drive circuit for driving a control electrode of each of said power semiconductor transistors to suppress driving current supplied to one of said at least two power semiconductor transistors when over current is detected in current flowing in at least another one of said at least two power semiconductor transistors connected in series,

wherein said plurality of power semiconductor transistors drive a fuel injection valve.

Claim 18 (currently amended): A semiconductor device ~~according to claim 15~~, comprising:

an embedded insulation layer formed in a semiconductor substrate;

a plurality of power semiconductor transistors formed on said semiconductor substrate;

a trench isolating between said plurality of power semiconductor transistors formed on said semiconductor substrate on said embedded insulation

layer, whereby said plurality of power semiconductor transistors are individually isolated from each other and, isolated from any other semiconductor transistors;

an isolator insulating and driving control electrodes of said power semiconductor transistors and including capacitive coupling provided for transmitting signals between said plurality of power semiconductors transistors;

wherein at least two of said plurality of power semiconductor transistors are each connected to each other in series; and

a drive circuit for driving a control electrode of each of said power semiconductor transistors to suppress driving current supplied to one of said at least two power semiconductor transistors when over current is detected in current flowing in at least another one of said at least two power semiconductor transistors connected in series,

wherein said plurality of power semiconductor transistors have an input control circuit supplying a control signal of a specific control pattern to said control electrodes of said plurality of power semiconductor transistors on the base of input signals.

Claim 19 (canceled).